MMIC Design and Technology Amplifier Design

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Data file for actual device

! FILENAME: N67300.S2P VERSION: 1.0
! NEC PART NUMBER: NE67300 DATE: 4/83
! BIAS CONDITIONS: VDS=3V, IDS=10mA
! NOTE : GATE AND DRAIN BOND WIRES ARE DE-EMBEDDED.
! NOTE : SOURCE BOND WIRE EFFECTS ARE INCLUDED. Ltotal = 0.07 nH
! (4 EACH 0.7 mil DIAMETER GOLD WIRES APPROXIMATELY 0.015" LONG).
GHZ S MA R 50

2	0.95	-26	3.79	161	0.04	79	0.59	-13
4	0.89	-50	3.26	141	0.06	66	0.58	-24
6	0.82	-70	2.83	126	0.08	56	0.54	-33
8	0.78	-88	2.55	114	0.09	51	0.5	-42
10	0.73	-102	2.21	104	0.1	48	0.47	-48
12	0.71	-114	2.16	93	0.1	43	0.45	-55
14	0.71	-122	2.11	90	0.11	44	0.47	-62
16	0.67	-128	1.92	76	0.11	43	0.49	-64
18	0.66	-140	1.81	63	0.11	40	0.52	-70

Stability

• Transistor is unstable when $|\Gamma_{in}| > 1$

$$\Gamma_{in} = \frac{b_1}{a_1} = S_{11} + \frac{S_{21}S_{12}\Gamma_L}{1 - S_{22}\Gamma_L}$$

Boundary Condition for Stability

$$S_{11} + \frac{S_{21}S_{12}\Gamma_L}{1 - S_{22}\Gamma_L} = 1$$

Stability

• Transistor is unstable when $|\Gamma_{out}| > 1$

$$\Gamma_{out} = \frac{b_2}{a_2} = S_{22} + \frac{S_{21}S_{12}\Gamma_s}{1 - S_{11}\Gamma_s}$$

Boundary Condition for Stability

$$\left| S_{22} + \frac{S_{21}S_{12}\Gamma_s}{1 - S_{22}\Gamma_s} \right| = 1$$

Stability Circles on Smith Chart

 Load or Source stability circle is the locus of points in the $\Gamma_{\rm L}$ or $\Gamma_{\rm s}$ plane, for which Γ_{in} or $\Gamma_{out} = 1$. If the center of the smith chart is enclosed by the stability circle then all points inside the circle are stable. If the center is not enclosed then all points inside the circle are unstable.

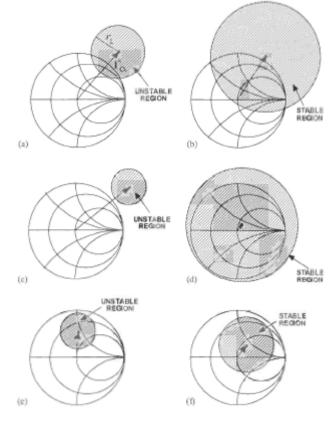


Figure 5.2 Stubility circles on the Smith chart: (a) stability circle partially inside the Smith chart, (b) partially inside and encompassing the 50 Ω point, (c) completely outside, (d) completely encompassing the Smith chart, (c) completely inside but not encompassing the 50 Ω point and (f) completely inside and encompassing the 50 Ω point

Unconditional Stability

 If all of the smith chart is in a stable region then the transistor is said to be unconditionally stable.

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$$\Gamma_{in}$$
 or Γ_{out} <1 for all values of Γ_L or Γ_S

$$K = \frac{1 - |S_{11}|^2 - |S_{22}|^2 + |\Delta|^2}{2|S_{12}S_{21}|}$$
$$\Delta = S_{11}S_{22} - S_{12}S_{21}$$

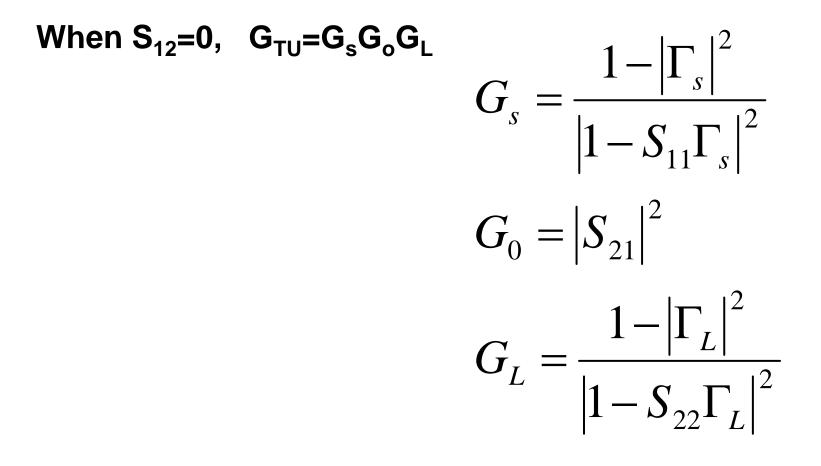
Unconditionally Stable for K>1

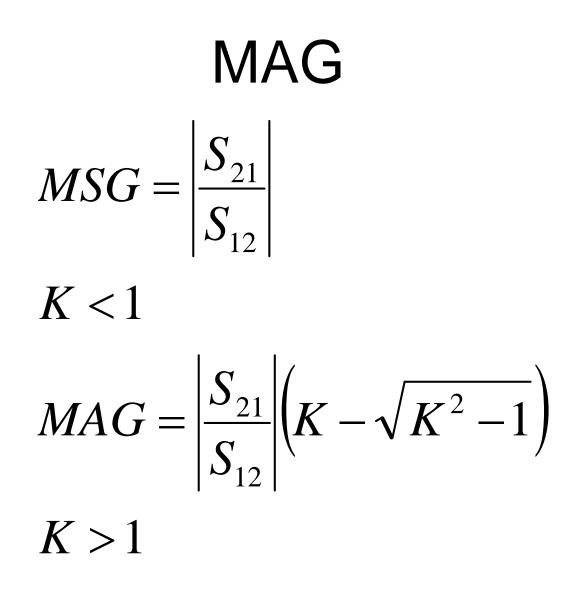
Constant Gain Circles

G_T= Power delivered to load / Power available from source

$$G_{T} = \frac{|S_{21}|^{2} \left(1 - |\Gamma_{s}|^{2}\right) \left(1 - |\Gamma_{L}|^{2}\right)}{\left|1 - S_{11}\Gamma_{s} - S_{22}\Gamma_{L} + \Delta\Gamma_{s}\Gamma_{L}\right|^{2}}$$

 G_{TU}



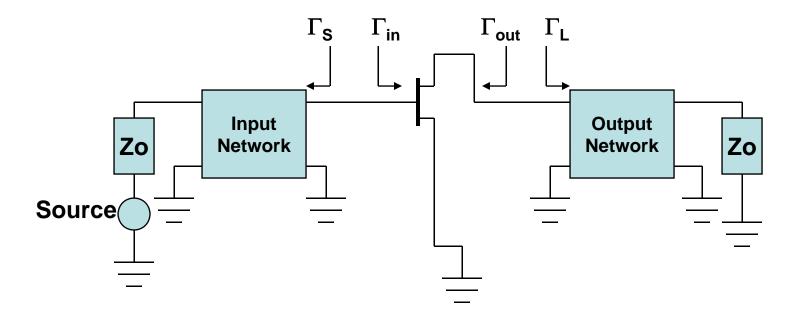


Noise Figure $F = F_{\min} + 4R_n \frac{\left|\Gamma_s - \Gamma_{opt}\right|^2}{\left(1 - \left|\Gamma_s\right|^2\right) 1 + \left|\Gamma_{opt}\right|^2}$

 F_{min} is noise figure at Γ_{opt} R_n is normalized "noise resistance" Circles of constant noise figure in Γ_s Plane

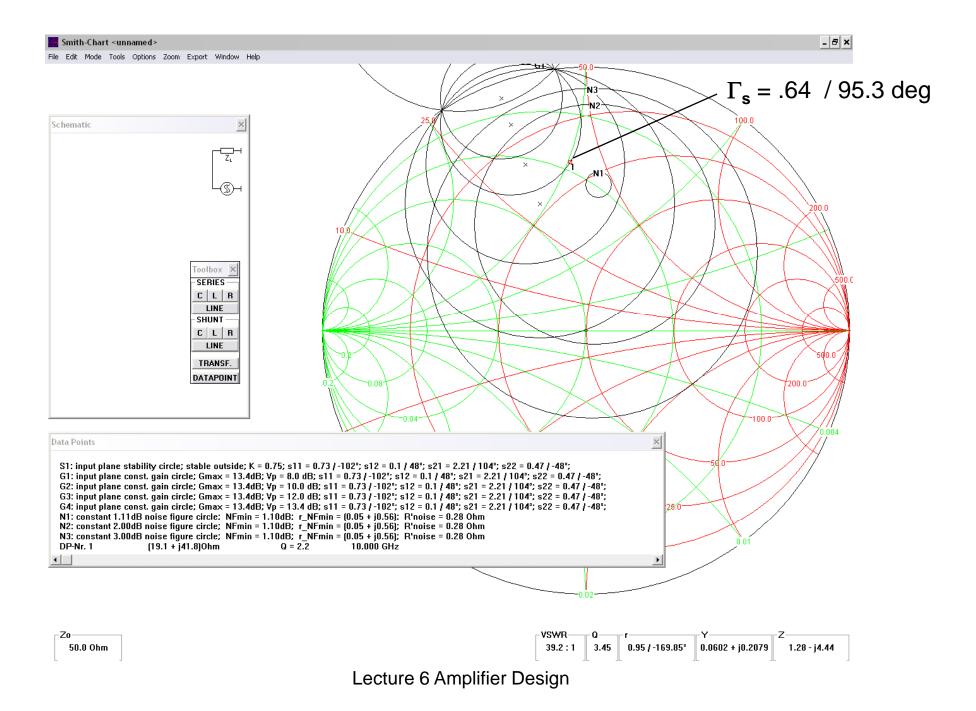
Device Data File

INEC PART NUMBER: NE67300 DATE: 4/83 ! BIAS CONDITIONS: VDS=3V, IDS=10mA **! NOISE PARAMETERS** ! NOTE : GATE AND DRAIN BOND WIRES ARE DE-EMBEDDED. ! NOTE : SOURCE BOND WIRE EFFECTS ARE INCLUDED. Ltotal = 0.07 nH (4 EACH 0.7 mil DIAMETER GOLD WIRES APPROXIMATELY 0.015" LONG). 1 0.40 .90 12 .57 2 0.40 .85 21 .51 4 0.40 .75 40 .44 FORMAT 6 0.60 .69 55 .38 GHz $NF_{min}dB$ $\Gamma_{opt}Mag$ $\Gamma_{opt}angle normalized Rn$ 8 0.80 .62 70 .33 10 1.10 .56 85 .28 12 1.40 .52 99 .24 14 1 70 49 114 20 16 2.00 .47 127 .18 18 2.25 .45 140 .16

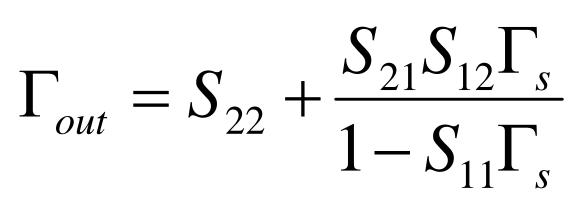


Design Γ_s and Γ_L to provide the desired performance May be a trade with stability, gain, noise figure Then design matching networks

- Plot on Γ_s plane
 - Source stability circle
 - Constant Gain circles
 - Constant Noise Figure circles
- Choose a suitable value of $\Gamma_{\rm s}$



• Calculate Γ_{out}



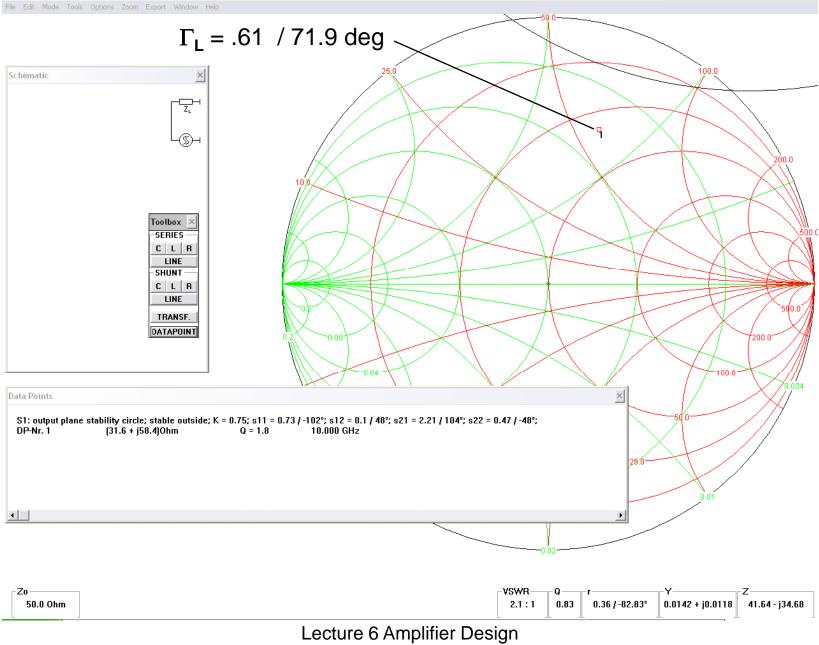
For example data

When $\Gamma_{\rm s}$ = .64 / 95.3 deg

 $\Gamma_{\rm out} = 0.61 / -71.9 \, \rm deg$

- Plot on Γ_L plane
 - Load stability circle
 - Conjugate of $\Gamma_{out} = \Gamma^*_{out}$
- If Γ^*_{out} is an allowed value for Γ_L – Choose $\Gamma_L = \Gamma^*_{out}$
- Else
 - Plot Constant Gain circle on Γ_L plane
 - Select a suitable value of $\Gamma_{\rm L}$





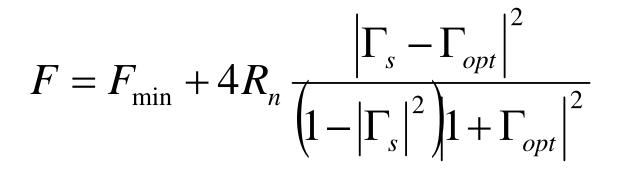
Calculate Gain

$$G_{T} = \frac{|S_{21}|^{2} \left(1 - |\Gamma_{s}|^{2}\right) \left(1 - |\Gamma_{L}|^{2}\right)}{\left|1 - S_{11} \Gamma_{s} - S_{22} \Gamma_{L} + \Delta \Gamma_{s} \Gamma_{L}\right|^{2}}$$

$$\Delta = S_{11} S_{22} - S_{12} S_{21}$$

For our example $G_T = 15.8$ 10Log $G_T = 12.0 \text{ dB}$

Calculate Noise Figure



Some useful Excel functions (must install Analysis ToolPak)

IMABS Returns the absolute value (modulus) of a complex number IMAGINARY Returns the imaginary coefficient of a complex number IMARGUMENT Returns the argument theta, an angle expressed in radians IMCONJUGATE Returns the complex conjugate of a complex number IMCOS Returns the cosine of a complex number IMDIV **Returns the quotient of two complex numbers** IMEXP Returns the exponential of a complex number Returns the natural logarithm of a complex number IMLOG10 Returns the base-10 logarithm of a complex number IMLOG2 Returns the base-2 logarithm of a complex number IMPOWER Returns a complex number raised to an integer power IMPRODUCT **Returns the product of from 2 to 29 complex numbers** IMRFAI Returns the real coefficient of a complex number IMSIN Returns the sine of a complex number IMSORT Returns the square root of a complex number IMSUB Returns the difference between two complex numbers IMSUM **Returns the sum of complex numbers** Lecture 6 Amplifier Design

Design Input and Output Network

- Input network transforms the source impedance such that $\Gamma_{\rm s}$ is presented to the transistor
- Output network transforms the load impedance such that $\Gamma_{\rm L}$ is presented to the transistor

Biasing

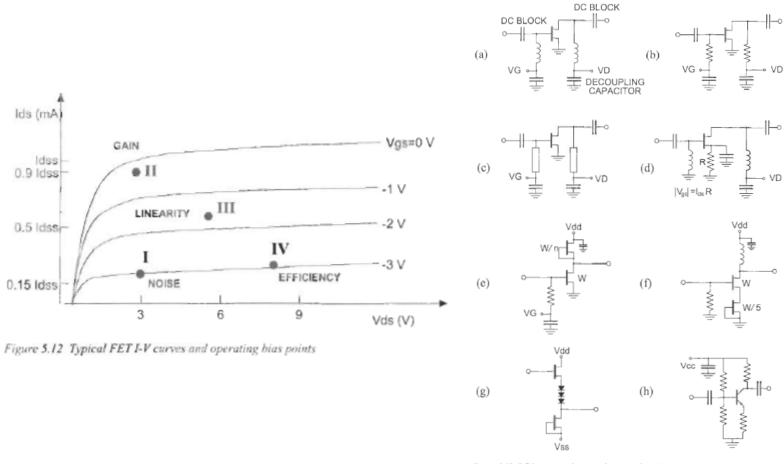


Figure 5.13 DC bias networks: (a) inductors as bias chokes, (b) high value resistors. (c) microstrip stubs, (d) self-biasing, (e) active load, (f) constant-current source self-biasing, (g) DC coupling and (h) bipolar transistor biasing